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DATE MAILED: 06/30/2004

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/800,180	03/12/2004	Yi Chung	8071-55 (OPP 030490US)	8614
7590 06/30/2004			EXAMINER	
F. CHAU & ASSOCIATES, LLP Suite 501			YEVSIKOV, VICTOR V	
	1900 Hempstead Turnpike		ART UNIT	PAPER NUMBER
East Meadow,	NY 11554		2825	

Please find below and/or attached an Office communication concerning this application or proceeding.

			W
	Application No.	Applicant(s)	/
	10/800,180	CHUNG, YI	
Office Action Summary	Examin r	Art Unit	
	Victor V Yevsikov	2825	
Th MAILING DATE of this communication a	ppears on the cover sheet w	ith the correspondence addres	S
Period for Reply	N V IO OFT TO EVOIDE • M	ONTHAN EDOM	
A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory perions - Failure to reply within the set or extended period for reply will, by state Any reply received by the Office later than three months after the main earned patent term adjustment. See 37 CFR 1.704(b).	J. 1.136(a). In no event, however, may a r eply within the statutory minimum of thir d will apply and will expire SIX (6) MON ute, cause the application to become AE	eply be timely filed by (30) days will be considered timely. THS from the mailing date of this commur ANDONED (35 U.S.C.§ 133).	nication.
Status			
1) Responsive to communication(s) filed on 12	<u>March 2004</u> .		
	nis action is non-final.		
3) Since this application is in condition for allow			rits is
closed in accordance with the practice under	r Ex parte Quayle, 1935 C.D). 11, 453 O.G. 213.	
Disposition of Claims			
4) Claim(s) 1-7 is/are pending in the application	١.		
4a) Of the above claim(s) is/are withdo	rawn from consideration.		
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1-7</u> is/are rejected. 7)□ Claim(s) is/are objected to.			
8) Claim(s) are subjected to.	or election requirement.		
Application Papers			
_			
 9) The specification is objected to by the Examination 10) The drawing(s) filed on 12 March 2004 is/are 		ected to by the Evaminer	
Applicant may not request that any objection to the		•	
Replacement drawing sheet(s) including the corre		` '	121(d).
11)☐ The oath or declaration is objected to by the	Examiner. Note the attached	Office Action or form PTO-1	52.
Priority under 35 U.S.C. § 119			
12)⊠ Acknowledgment is made of a claim for foreig	an priority under 35 U.S.C. 8	119(a)-(d) or (f).	
a) All b) Some * c) None of:		(-) (-)	
 Certified copies of the priority docume 	nts have been received.		
2. Certified copies of the priority docume			
3. ☐ Copies of the certified copies of the pr	•	received in this National Stag	je
application from the International Bure * See the attached detailed Office action for a lie		raccivad	
See the attached detailed Office action for a list	st of the certified copies not	received.	
Attachment(s)			
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)		ummary (PTO-413) s)/Mail Date	
2) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0	8) 5) Notice of Ir	nformal Patent Application (PTO-152))
Paper No(s)/Mail Date	6) Other:	_ . .	

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DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

Claims 1, 2 and 4 are rejected under 35 U.S.C. 102(a) as being anticipated by Kim et al. (U.S. 2003/0223019 A1).

With respect to claims 1, 2 and 4 Kim teaches a thin film transistor array panel comprising:

- a substrate 110;
- a gate electrode 124;
- a gate insulating layer 140 formed on the gate electrode 124;
- a polysilicon layer 154 formed on the gate insulating layer 140 and including a pair of ohmic contact areas 163, 165 doped with n type conductive impurity;

source 173 and drain 175 electrodes formed on the ohmic contact areas 163, 165 at least in part;

a passivation layer 180 formed on the source and the drain electrodes and having a contact holes 181-183 exposing the drain electrode at least in part; and a pixel electrode 190 formed on the passivation layer and connected to the drain

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electrode 175 through the contact hole 183, wherein:

the conductive impurity comprises boron or phosphorous;

a gate line disposed between the substrate and the gate insulating layer and connected to the gate electrode; and a data line disposed between the gate insulating layer and the passivation layer and connected to the source electrode.

Reference: abstract; fig. 2 with corresponding text.

Claims 5 – 7 are rejected under 35 U.S.C. 102(a) as being anticipated by Park (U.S. 2002/0097349 A1).

With respect to claims 5-7 Park teaches a method of manufacturing a thin film transistor array panel, the method comprising:

forming a gate electrode 24;

depositing a gate insulating layer 30and a polysilicon layer 40 on the gate electrode in sequence;

forming a photoresist having a first portion 112 and a second portion 114 thinner than the first portion on the polysilicon layer;

patterning the polysilicon layer using the photoresist as a mask to form a semiconductor layer 40;

removing the second portion of the photoresist;

performing impurity implantation using the first portion of the photoresist as a mask to form ohmic contact areas in the semiconductor layer;

removing the first portion of the photoresist;

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forming source 65 and drain 66 electrodes on the ohmic contact areas;

forming a passivation layer 72 having a contact hole 71 on the drain electrode;

and

forming a pixel electrode 82 on the passivation layer; and wherein:

the formation of the photoresist comprising coating a photoresist film on the polysilicon layer;

exposing the photoresist film through a photo-mask having a slit pattern or a translucent portion facing the second portion of the photoresist;

developing the photoresist film to form the photoresist;

the impurity comprises p type conductive impurity.

Reference: figs. 3, 5A-5g with corresponding text.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 3 is rejected as being prima facie obvious without showing that the claimed impurity ranges achieve unexpected results relative to the prior art range.

In re Woodruff, 16 USPQ2d 1935, 1937 (Fed. Cir. 1990). See also In re Huang, 40 USPQ2d 1685, 1688 (Fed. Cir. 1996) (claimed ranges of a result effective variable, which do not overlap the prior art ranges, are unpatentable unless they produce a new

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and unexpected result which is different in kind and not merely in degree from the results of the prior art). See also In re Boesch, 205 USPQ 215 (CCPA 1980) (discovery of optimum value of result effective variable in known process is ordinarily within skill of art) and In re Aller, 105 USPQ 233 (CCPA 1955) (selection of optimum ranges within prior art general conditions is obvious).

Therefore, to select the top silicon layer as being thicker is seen as an obvious development over prior art as the changing of dimension has not been shown to produce unexpected results.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Victor Yevsikov whose telephone number is (571) 272-1910. The examiner can normally be reached on Monday –Thursdays 8:00-5:30.

If attempts to reach the examiner by telephone are unsuccessful, examiner's supervisor, Matthew S. Smith, can be reached on (571) 272-1907. The fax phone numbers for the organization where this application or processing is assigned is (703) 873-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published application may be obtained from either Private PAIR or Public PAIR. Status information for unpublished application is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on

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access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Victor Yevsikov

Examiner

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June 22, 2004

CARIDAD EVERYALT PHINARY EXAMINED